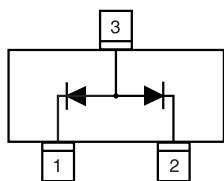
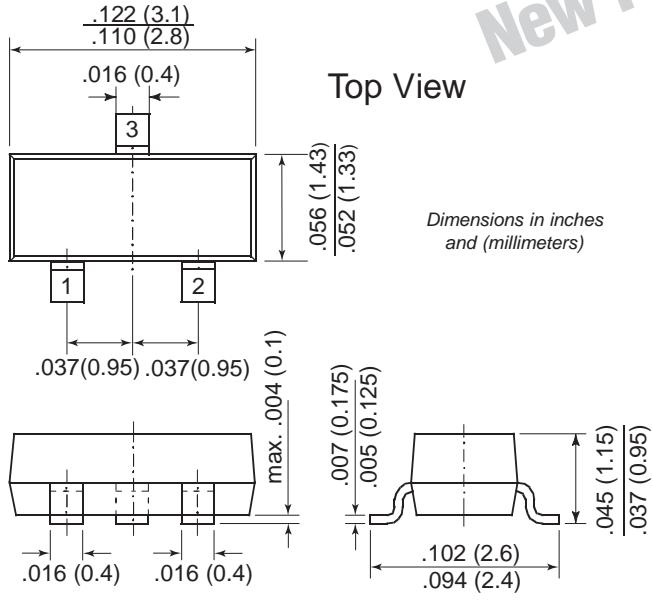
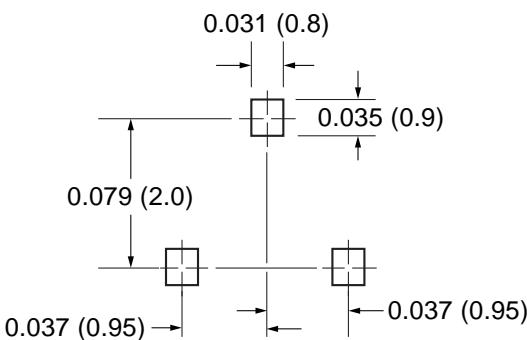



**TO-236AB (SOT-23)**

**Top View**

### Mounting Pad Layout



### Features

- Silicon Epitaxial Planar Diode
- Fast switching dual common-anode diode, especially suited for applications requiring high voltage capability

### Mechanical Data

**Case:** SOT-23 (TO-236AB) Plastic Package

**Weight:** approx. 0.008g

**Marking Code:** DBA

**Packaging Codes/Options:**

E8/10K per 13" reel (8mm tape), 30K/box

E9/3K per 7" reel (8mm tape), 30K/box

### Maximum Ratings and Thermal Characteristics

T<sub>A</sub> = 25°C unless otherwise noted

| Parameter   | Symbol           | Value              | Unit |
|---|------------------|--------------------|------|
| Continuous Reverse Voltage                                    | V <sub>R</sub>   | 240                | V    |
| Peak Repetitive Reverse Voltage                               | V <sub>RMM</sub> | 300                | V    |
| Peak Repetitive Reverse Current                               | I <sub>RMM</sub> | 200                | mA   |
| Forward Current (continuous)                                  | I <sub>F</sub>   | 225                | mA   |
| Peak Repetitive Forward Current                               | I <sub>RFM</sub> | 625                | mA   |
| Non-Repetitive Peak Forward Current at tp = 1μs<br>at tp = 1s | I <sub>FSM</sub> | 4.0<br>1.0         | A    |
| Power Dissipation   | P <sub>tot</sub> | 350 <sup>(1)</sup> | mW   |
| Typical Thermal Resistance Junction to Ambiant Air            | R <sub>θJA</sub> | 357 <sup>(1)</sup> | °C/W |
| Junction Temperature  | T <sub>j</sub>   | 150                | °C   |
| Storage Temperature Range                                     | T <sub>s</sub>   | -65 to +150        | °C   |

**Note:**

(1) Device on Fiberglass Substrate, see layout on bottom of second page

# Dual Common-Anode Small Signal Switching Diode

## Electrical Characteristics

$T_J = 25^\circ\text{C}$  unless otherwise noted

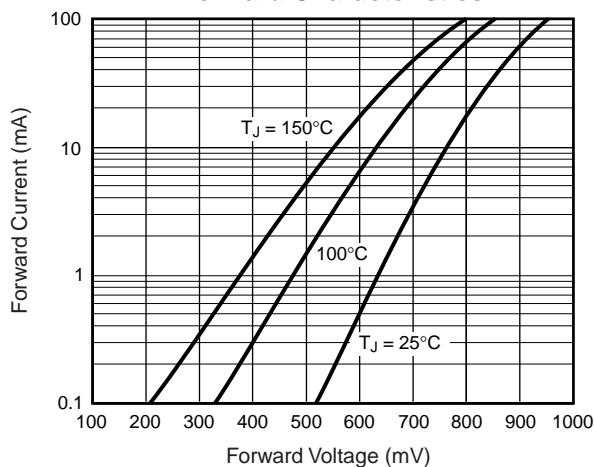
| Parameter                 | Symbol    | Test Condition  | Min | Typ  | Max          | Unit                |
|---------------------------|-----------|---|-----|------|--------------|---------------------|
| Reverse Breakdown Voltage | $V_{BR}$  | $I_R = 100\mu\text{A}$  | 300 | —    | —            | V                   |
| Leakage Current           | $I_R$     | $V_R = 240\text{V}$<br>$V_R = 240\text{V}, T_J = 150^\circ\text{C}$   | —   | —    | 100<br>100   | nA<br>$\mu\text{A}$ |
| Forward Voltage           | $V_F$     | $I_F = 20\text{mA}$<br>$I_F = 100\text{mA}$                           | —   | 0.83 | 0.87<br>1.00 | V                   |
| Capacitance               | $C_{tot}$ | $V_F = V_R = 0, f = 1\text{MHz}$                                      | —   | —    | 5.0          | pF                  |
| Reverse Recovery Time     | $t_{rr}$  | $I_F = I_A = 30\text{mA}$<br>$I_{rr} = 3.0\text{mA}, R_L = 100\Omega$ | —   | —    | 50           | ns                  |

(1) Device on fiberglass substrate, see layout at bottom of page

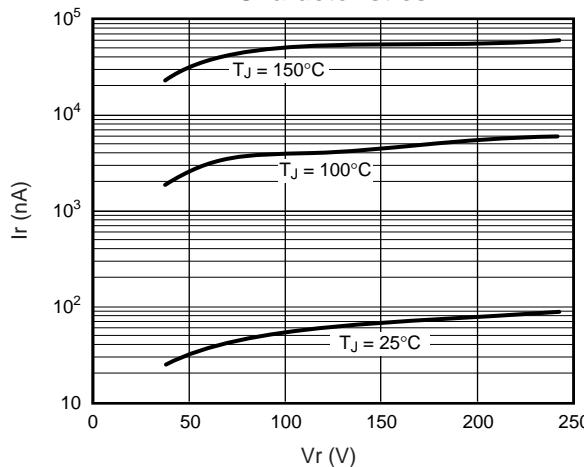
## Ratings and Characteristic Curves

$(T_A = 25^\circ\text{C}$  unless otherwise noted)

**Fig. 1 – Typical Instantaneous Forward Characteristics**

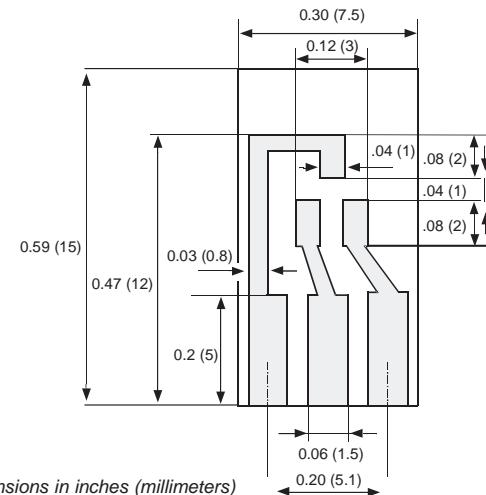


**Fig. 2 – Typical Reverse Characteristics**



### Layout for $R_{\theta JA}$ test

Thickness:  
Fiberglass 0.059 in. (1.5 mm)  
Copper leads 0.012 in. (0.3 mm)



Dimensions in inches (millimeters)